





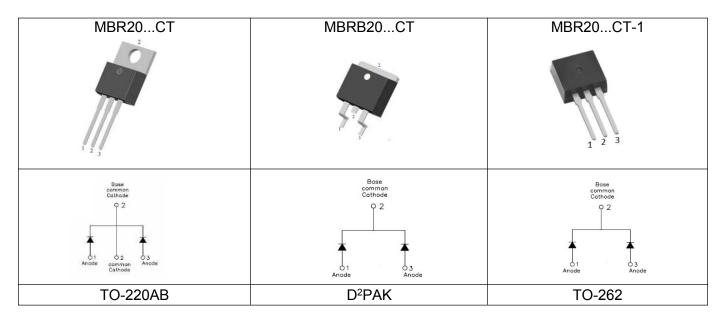
# MBR2050/2060CT MBRB2050CT MBR2050/2060CT-1 SCHOTTKY RECTIFIER

#### **Features**

- 150°C T<sub>J</sub> operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- . All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

#### **Applications**

- · Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection



#### **Maximum Ratings:**

Characteristics	Symbol	Condition		Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage	V <sub>RRM</sub> V <sub>RWM</sub>	-	50	MBR2050CT	
DC Blocking Voltage	VRWM VR		60	MBR2060CT	ľ
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @Tc=80°C,		10Per Leg)	Α
g	-1 (/(۷)	rectangular wave form	- :	20(Per Device)	
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I <sub>FSM</sub>	8.3ms, Half Sine pulse	150		А

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#### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop (per leg)*	V <sub>F1</sub>	@ 10A, Pulse, T <sub>J</sub> = 25 °C @ 20A, Pulse, T <sub>J</sub> = 25 °C	0.66 0.85	0.80 0.95	V
	V <sub>F2</sub>	@ 10A, Pulse, T <sub>J</sub> = 125 °C @ 20A, Pulse, T <sub>J</sub> = 125 °C	0.61 0.75	0.70 0.85	V
Reverse Current (per leg)*	I <sub>R1</sub>	$@V_R = \text{rated } V_R$ $T_J = 25 °C$	0.075	1.0	mA
	I <sub>R2</sub>	$@V_R = \text{rated } V_R$ $T_J = 125 ^{\circ}C$	4	150	mA
Junction Capacitance (per leg)	Ст	@V <sub>R</sub> = 5V, T <sub>C</sub> = 25 $^{\circ}$ C f <sub>SIG</sub> = 1MHz	260	400	pF
Series Inductance (per leg)	Ls	Measured lead to lead 5 mm from package body	8.0	-	nΗ
Max. Voltage Rate of Change	dv/dt	-	-	10,000	V/µs

 $<sup>^*</sup>$  Pulse width < 300  $\mu$ s, duty cycle < 2%

#### **Thermal-Mechanical Specifications:**

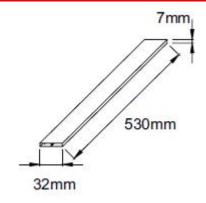
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R <sub>θ</sub> JC	DC operation	2.3	°C/W
Typical Thermal Resistance Case to Heat Sink	R <sub>0</sub> CS	Mounting surface, smooth and greased(only for TO-220)	0.50	°C/W
Case Style	TO-220AB D <sup>2</sup> PAK TO-262			

# **Tube Specification**

Device	Package	Weight	Shipping
MBR20CT	TO-220AB	1.8g	50pcs / tube
MBRB20CT	D <sup>2</sup> PAK	1.85g	800pcs / reel
MBR20CT-1	TO-262	1.85g	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

# **Tube Specification(TO-220AB/TO-262)**



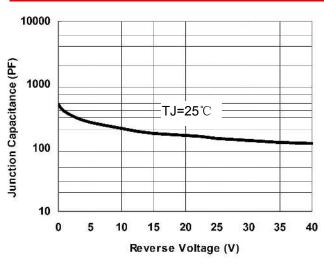
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#### **Ratings and Characteristics Curves**



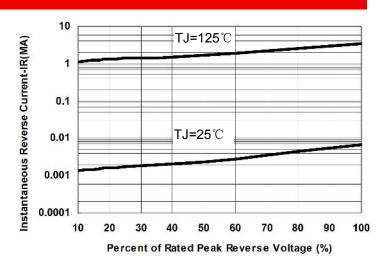


Fig.1-Typical Junction Capacitance

Fig.2-Typical Reverse Characteristics

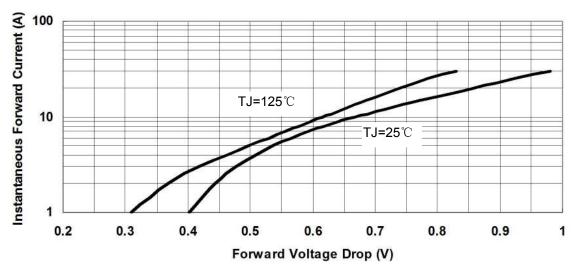
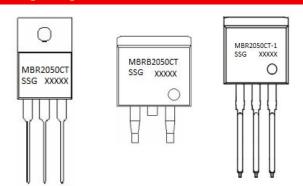


Fig.3-Typical Instantaneous Forward Voltage Characteristics

#### **Marking Diagram**



Where XXXXX is YYWWL

MBR = Device Type
B = Package type
20 = Forward Current (20A)
50 = Reverse Voltage (50V)
CT-1 = Configuration
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

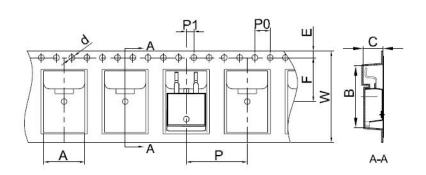
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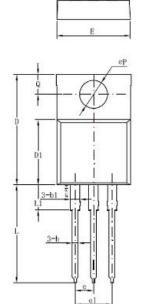


# Carrier Tape Specification D<sup>2</sup>PAK

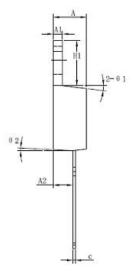


Symbol	Millimeters			
	Min.	Max.		
Α	10.70	10.90		
В	16.03	16.23		
С	5.11	5.31		
d	1.45	1.65		
E	1.65	1.85		
F	11.40	11.60		
P0	3.90	4.10		
Р	15.90	16.10		
P1	1.90	2.10		
W	23.90	24.30		

# **Mechanical Dimensions TO-220AB**



2 0 3



Symbol	Millimeters			
- Cymbol	Min.	Typical	Max.	
Α	4.42	4.57	4.72	
A1	1.17	1.27	1.37	
A2	2.52	2.69	2.89	
b	0.71	0.81	0.96	
b1	1.17	1.27	1.37	
С	0.31	0.38	0.61	
D	14.94	15.24	15.54	
D1	8.85	9.00	9.15	
E	10.01	10.16	10.31	
е		2.54		
e1	4.98	5.06	5.18	
H1	6.04	6.24	6.44	
L	12.7	13.56	13.80	
L1	3.56	3.5	3.96	
ФР	3.74	3.84	4.04	
Q	2.54	2.74	2.94	
Θ1		7°		
Θ2		3°		
Θ3		4°		

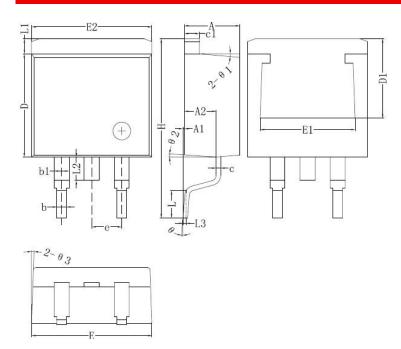
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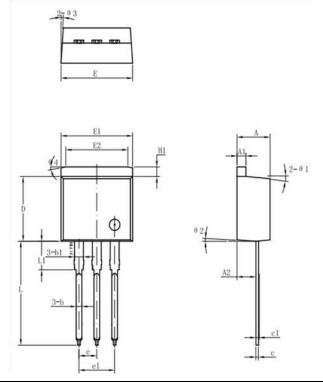


# **Mechanical Dimensions D<sup>2</sup>PAK**



Symbol	Millimeters			
	Min.	Typical	Max.	
Α	4.47	4.70	4.85	
A1	0	0.10	0.25	
A2	2.59	2.69	2.89	
b	0.71	0.81	0.96	
b1	1.17	1.27	1.37	
С	0.31	0.38	0.61	
c1	1.17	1.27	1.37	
D	8.50	8.70	8.90	
D1	6.40			
E	10.01	10.16	10.31	
E1	7.6			
E2	9.98	10.08	10.31	
е		2.54		
Н	14.6	15.1	15.6	
L	2.00	2.30	2.74	
L1	1.12	1.27	1.42	
L2	1.30		2.20	
L3		0.25BSC		
е	0	-	8°	
e1		5°		
e2		4°		
e3		4°		

# **Mechanical Dimensions TO-262**



Cumbal	Millimeters				
Symbol	Min.	Typical	Max.		
Α	4.55	4.70	4.85		
A1	0	0.10	0.25		
A2	2.59	2.69	2.89		
b	0.71	0.81	0.96		
b1		1.27			
С	0.36	0.38	0.61		
c1	1.17	1.27	1.37		
D	8.55	8.70	8.85		
D1	6.40				
E	10.01	10.16	10.31		
E1	7.6				
E2	9.98	10.08	10.18		
е		2.54			
Н	14.6	15.1	15.6		
L	2.00	2.30	2.70		
L1	1.17	1.27	1.40		
L2			2.20		
L3		0.25BSC			
е	0	-	8°		
e1		5°			
e2		4°			
e3		4°			

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# MBR2050/2060CT MBRB2050CT MBR2050/2060CT-1

#### Technical Data Data Sheet N0034, Rev. B





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